

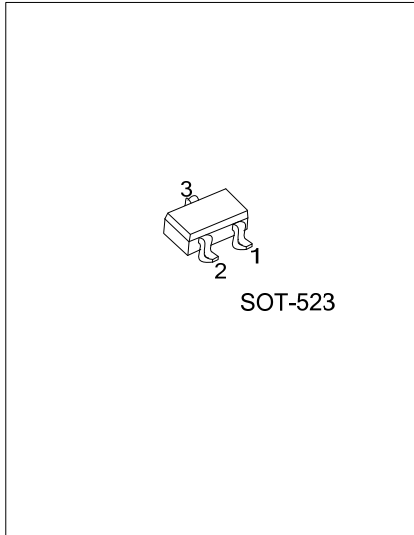


2N7002ZT

Preliminary

Power MOSFET

300m Amps, 60 Volts DUAL N-CHANNEL ENHANCEMENT MODE MOSFET



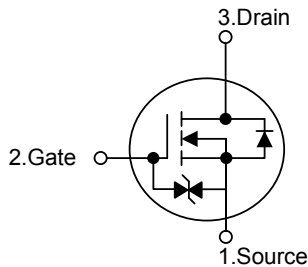
DESCRIPTION

The UTC **2N7002ZT** uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate voltages during operation. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * Low Reverse Transfer Capacitance (C_{RSS} = typical 3.0 pF)
- * ESD Protected
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL

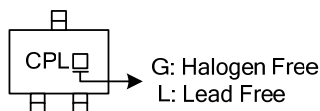


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N7002ZTL-AN3-R	2N7002ZTG-AN3-R	SOT-523	S	G	D	Tape Reel

<p>2N7002ZTG-AL6-R</p> <p>(1) Packing Type (2) Package Type (3) Halogen Free</p>	<p>(1) R: Tape Reel (2) AL6: SOT-363 (3) G: Halogen Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	Continuous	300	mA
	Pulse(Note 2)	800	
Power Dissipation Derating above $T_A=25^\circ\text{C}$	P_D	200	mW
		1.6	mW/ $^\circ\text{C}$
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V, I_D=10\mu\text{A}$	60			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=10V, I_D=1\text{mA}$	1.0	1.85	2.5	V
Static Drain-Source On-Resistance (Note)	$R_{DS(ON)}$	$V_{GS}=10V, I_D=0.5A, T_J=125^\circ\text{C}$			13.5	Ω
		$V_{GS}=5V, I_D=0.05A$			7.5	
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1.0\text{MHz}$		25	50	pF
Output Capacitance	C_{OSS}			10	25	pF
Reverse Transfer Capacitance	C_{RSS}			3.0	5.0	pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{D(ON)}$	$I_D=0.2\text{A}, V_{DD}=30V, V_{GS}=10V,$		12	20	ns
Turn-OFF Delay Time	$t_{D(OFF)}$	$R_L=150\Omega, R_G=10\Omega$		20	30	ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=115\text{mA}$ (Note)		0.88	1.5	V
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				0.8	A
Maximum Continuous Drain-Source Diode Forward Current	I_S				115	mA

Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

2. Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 1\%$

■ TEST CIRCUITS AND WAVEFORMS

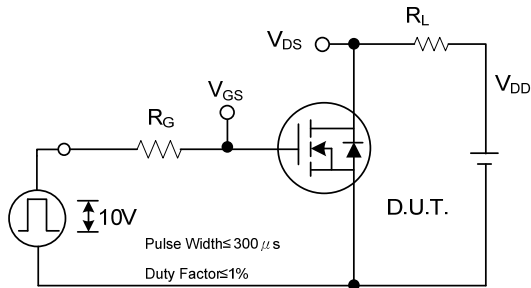


Fig. 2A Switching Test Circuit

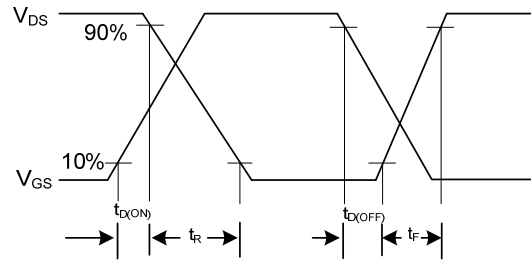


Fig. 2B Switching Waveforms

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